

Samsung 3D V-NAND Gets Enterprise Use

Written by Marco Attard
16 August 2013

Samsung is quick to find applications for its [recently announced 3D Vertical NAND](#) (3D V-NAND)-- the company reveals an enterprise SSD carrying the technology at the Flash Memory Summit 2013.



"By applying our 3D V-NAND Samsung is providing its global customers with high density and exceptional reliability, as well as an over 20% performance increase and an over 40% improvement in power consumption," the company says. "As we pioneer a new era of memory technology, we will continue to introduce differentiated green memory products and solutions for the server, mobile and PC markets to help reduce energy waste and to create greater shared value in the enterprise and for consumers."

The technology combines a proprietary vertical cell structure based on 3D Charge Trap Flash (CTF) technology and the vertical interconnect process-- and promises twice the scaling of 20nm-class planar NAND flash, beating the scaling limits of traditional NAND flash products caused by cell-to-cell interference, allowing for 128Gb density on a single chip.

The V-NAND SSDs will be available in 480 and 960GB versions. Samsung claims the 960GB version offers 20% faster sequential and random write speeds over a 6Gbps SATA interface as well as 35K program erase cycles, all inside a 2.5-inch form factor.

Go [Samsung Introduces First 3D V-NAND Based SSD for Enterprise](#)